International **IOR** Rectifier

HEXFRED[™]

Features

- Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- · Guaranteed Avalanche
- · Specified at Operating Conditions
- Benefits
- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- Reduced Snubbing
- Reduced Parts Count

Description

International Rectifier's HFA16TB120 is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 volts and 16 amps continuous current, the HFA16TB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA16TB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

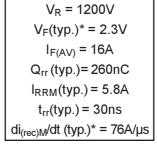
Absolute Maximum Ratings

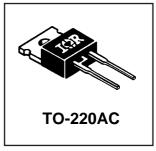
	Parameter	Max.	Units
V _R	Cathode-to-Anode Voltage	1200	V
I _F @ T _C = 25°C	Continuous Forward Current		
I _F @ T _C = 100°C	Continuous Forward Current	16	
I _{FSM}	Single Pulse Forward Current	190	A
I _{FRM}	Maximum Repetitive Forward Current	64	
I _{AS} ①	Maximum Single Pulse Avalanche Current	16	
P _D @ T _C = 25°C	Maximum Power Dissipation	151	w
P _D @ T _C = 100°C	Maximum Power Dissipation	60	
TJ	Operating Junction and	EE to 11E0	°C
T _{STG}	Storage Temperature Range	-55 to +150	

Preliminary Data Sheet PD -2.492 05/97

HFA16TB120

Ultrafast, Soft Recovery Diode





* 125°C

Electrical Characteristics @ $T_J = 25^{\circ}C$ (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions	
V _{BR}	Cathode Anode Breakdown Voltage	1200			V	I _R = 100μA	
	Max Forward Voltage		2.5	3.0	V	I _F = 16A	
V_{FM}			3.2	3.93		I _F = 32A See Fig. 1	
			2.3	2.7		I _F = 16A, T _J = 125°C	
I _{RM}	Max Reverse Leakage Current		0.75	20	μA	V _R = V _R Rated See Fig. 2	
			375	2000		T_J = 125°C, V_R = 0.8 x V_R Rated	
CT	Junction Capacitance		27	40	pF	V _R = 200V See Fig. 3	
L _S	Series Inductance		8.0		nH	Measured lead to lead 5mm from	
	Series Inductance					package body	

Dynamic Recovery Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions		
t _{rr}	Reverse Recovery Time See Fig. 5, 10		30			I_F = 1.0A, di _f /dt = 200A/µs, V _R = 30V		
t _{rr1}			90	135	ns	T _J = 25°C		
t _{rr2}			164	245		T _J = 125°C	I _F = 16A	
I _{RRM1}	Peak Recovery Current		5.8	10	А	T _J = 25°C		
I _{RRM2}	See Fig. 6		8.3	15	~	T _J = 125°C	V _R = 200V	
Q _{rr1}	Reverse Recovery Charge See Fig. 7		260	675	nC	T _J = 25°C	di _f /dt = 200A/µs	
Q _{rr2}			680	1838	no	T _J = 125°C		
di _{(rec)M} /dt1	Peak Rate of Fall of Recovery Current		120		A/us	T _J = 25°C		
di _{(rec)M} /dt2	During t _b See Fig. 8		76		Λμs	T _J = 125°C		

Thermal - Mechanical Characteristics

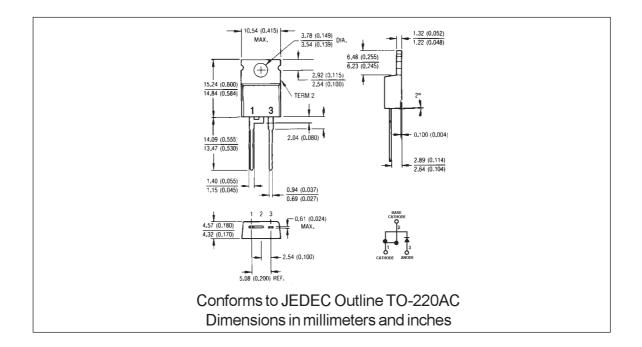
	Parameter	Min.	Тур.	Max.	Units
T _{lead} ②	Lead Temperature			300	°C
R _{θJC}	Thermal Resistance, Junction to Case			0.83	
R _{0JA} ③	Thermal Resistance, Junction to Ambient			80	K/W
R _{θCS} ⊕	Thermal Resistance, Case to Heat Sink		0.50		
Wt	Weight		2.0		g
	VVCigit		0.07		(oz)
	Mounting Torque	6.0		12	Kg-cm
		5.0		10	lbf•in

 \odot L=100µH, duty cycle limited by max T_J

- ② 0.063 in. from Case (1.6mm) for 10 sec
- ③ Typical Socket Mount
- ④ Mounting Surface, Flat, Smooth and Greased

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International **TOR** Rectifier



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 Data and specifications subject to change without notice.